AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-61 (Canceled).

62. (New) A nitride semiconductor light emitting device comprising;

a substrate,

a first nitride semiconductor layer having an impurity concentration within $1 \times 10^{17}/cm^3$, said first nitride semiconductor layer being a single layer,

a second nitride semiconductor layer having an n-type electrode, said second nitride semiconductor layer being a single layer,

a third nitride semiconductor layer having an impurity concentration within $1 \times 10^{17}/cm^3$, said third nitride semiconductor layer being a super lattice layer of InGaN layers and GaN layers.

63. (New) The nitride semiconductor light emitting device according to claim 62;

wherein said second nitride semiconductor layer is made of GaN or AlGaN and said second nitride semiconductor layer includes Si as an n-type impurity.

64. (New) The nitride semiconductor light emitting device according to claim 62;

wherein said first nitride semiconductor layer is made of GaN or AlGaN.

65. (New) The nitride semiconductor light emitting device according to claim 62; wherein said second nitride semiconductor layer has an carrier concentration more than 3 X $10^{18}/cm^3$.

66. (New) The nitride semiconductor light emitting device according to claim 62; wherein said second nitride semiconductor layer has a resistivity less than 8 x 10^{-3} ohm • cm.

67. (New) The nitride semiconductor light emitting device according to claim 62; further comprising a buffer layer between said substrate and said first nitride semiconductor layer.

68. (New) The nitride semiconductor light emitting device according to claim 62; wherein said first nitride semiconductor layer has a thickness within a range of from 0.l to 20 μm.

69. (New) The nitride semiconductor light emitting device according to claim 62; wherein said second nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm,

70. (New) A nitride semiconductor light emitting device comprising:

a substrate,

a first nitride semiconductor layer having an impurity concentration within 1 X $10^{17}/cm^3$, said first nitride semiconductor layer being a single layer,

a second nitride semiconductor layer having an n-type electrode, said second nitride semiconductor layer being a single layer,

a third nitride semiconductor layer having an impurity concentration within 1 X $10^{17}/cm^3$, said third nitride semiconductor layer being a super lattice layer of GaN layers.

71. (New) The nitride semiconductor light emitting device according to claim 70; wherein said second nitride semiconductor layer is made of GaN or AlGaN and said second nitride semiconductor layer includes Si as an n-type impurity.

72. (New) The nitride semiconductor light emitting device according to claim 70; wherein said first nitride semiconductor layer is made of GaN or AlGaN

73. (New) The nitride semiconductor light emitting device according to claim 70; wherein said second nitride semiconductor layer has an carrier concentration more than 3 X $10^{18}/cm^3$.

74. (New) The nitride semiconductor light emitting device according to claim 70; wherein said second nitride semiconductor layer has a resistivity less than 8 X 10^{-3} ohm · cm.

75. (New) The nitride semiconductor light emitting device according to claim 70;

further comprising a buffer layer between said substrate and said first nitride semiconductor layer.

76. (New) The nitride semiconductor light emitting device according to claim 70; wherein said first nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm,

77. (New) The nitride semiconductor light emitting device according to claim 70; wherein said second nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm.

78. (New) The nitride semiconductor light emitting device according to claim 70; wherein said third nitride semiconductor layer being a super lattice layer of undoped GaN layers and Si doped GaN layers.

AMENDMENTS TO THE DRAWINGS

The attached sheet of drawings includes changes to Figs. 1 and 2. This sheet, which includes Figs. 1 and 2, replaces the original sheet including Figs. 1 and 2.

Attachment: Replacement Sheet(s)